

GENERAL DESCRIPTION

The 2005 is a common base transistor capable of providing 5 watts of CW RF output power at 2000 MHz. This hermetically sealed transistor is specifically designed for Class C amplifier applications. It utilizes gold metallization and diffused ballasting to provide high reliability and supreme ruggedness.

2005
5.0 WATTS - 28 VOLTS
2000 MHz

MICROWAVE CW BIPOLAR

ABSOLUTE MAXIMUM RATINGS

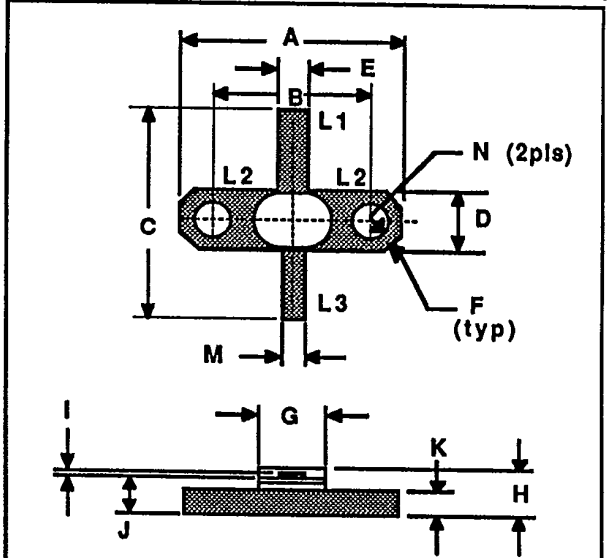
Maximum Power Dissipation @ 25°C Case Temperature 20 W

Maximum Voltage and Current

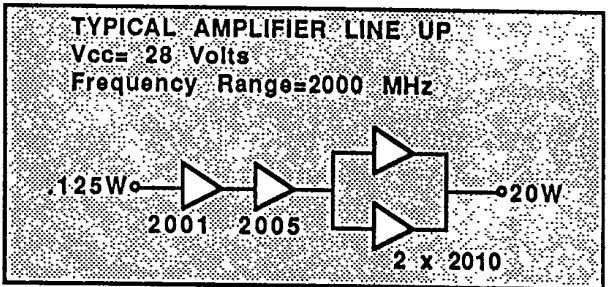
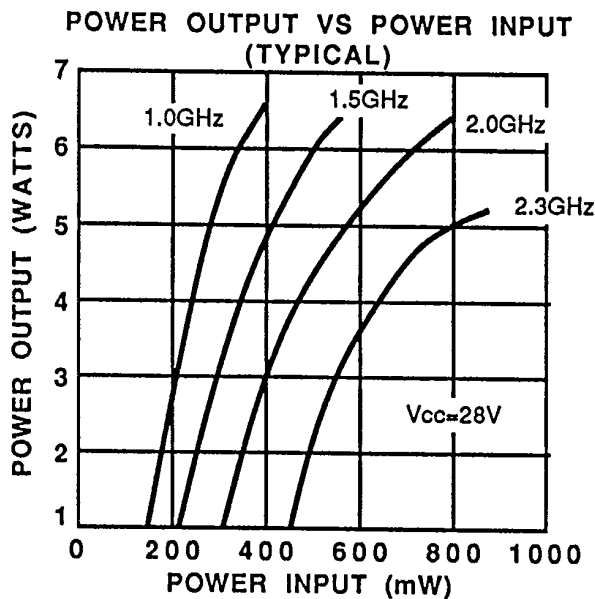
BVces Collector to Emitter Voltage 50 V
 BVebo Emitter to Base Voltage 3.5 V
 Ic Collector Current 1.0 A

Maximum Temperatures

Storage Temperature -65 to +200°C
 Operating Junction Temperature +200°C

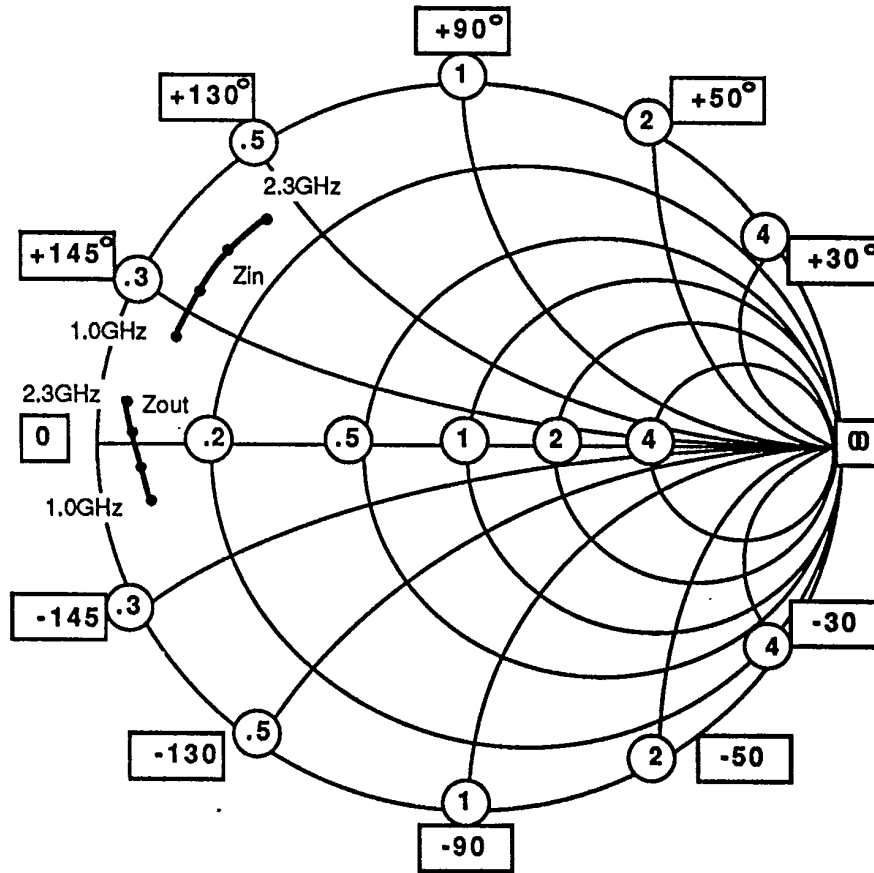


DIM	Millimeter	TOL	Inches	TOL	
L1 : B	A	20.32	.13	.800	.005
L2 : E	B	14.27	.13	.562	.005
L3 : C	C	18.03	MIN	.710	MIN
	D	5.84	.13	.230	.005
	E	3.05	.13	.120	.005
	F	45°	5°	45°	5°
	G	5.84	.13	.230	.005
	H	4.57	REF	.180	REF
	I	0.13	.02	.005	.001
	J	3.81	.13	.150	.005
	K	1.52	.13	.060	.005
	M	1.27	.13	.050	.005
	N	3.30	.13	.130	.005



**SMITH CHART
2005**

NORMALIZED IMPEDANCE AND ADMITTANCE COORDINATES



NORMALIZED TO A 50 OHM SYSTEM.